

Abstract Submitted  
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**Spin dependent tunnelling in indirect double-barrier structures**

TITUS SANDU, Departement de Chimie, Universite de Montreal, Canada — Spin-dependent tunnelling and polarization in GaAs/AlAs/GaAs based resonant tunnelling diode are studied by a tight-binding model. We compare the GaAs/AlAs/GaAs case with similar structures where the barriers are direct and show the advantages of a GaAs/AlAs/GaAs configuration.

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